

| L Number | Hits | Search Text   | DB  | Time stamp       |
|----------|------|---|---|------------------|
| 5        | 32   | "sealant material" adj "epoxy"                          | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 16:30 |
| 6        | 0    | "liquid crystal" adj "sealant material"<br>adj "epoxy"  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 16:30 |
| 7        | 0    | "liquid crystal" adj "sealant material"                 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 16:31 |
| 8        | 3    | "liquid crystal" near "sealant material"                | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 16:31 |
| -        | 2    | "6330099"   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 16:28 |
| -        | 2    | "6362861"   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 10:29 |
| -        | 2231 | "Agilent Technologies".AS.                              | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 10:36 |
| -        | 0    | "Agilent Technologies".AS. and 349/190                  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 10:37 |
| -        | 0    | "anisotropic etch" adj "filling hole"                   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 10:46 |
| -        | 0    | "anisotropic etch" adj "liquid crystal<br>filling hole" | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 10:47 |
| -        | 0    | "anisotropic etch" adj "liquid crystal"                 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 10:48 |
| -        | 153  | (349/190).CCLS.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 15:20 |
| -        | 440  | (438/30).CCLS.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 12:46 |
| -        | 1    | "anisotropic etch" adj "silicon wafer"                  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 12:55 |

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| - | 3   | "anisotropic etch" near "silicon wafer"               | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 12:56 |
| - | 61  | "anisotropic etching" adj "silicon wafer"             | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 13:14 |
| - | 0   | "anisotropic etching" near "liquid crystal"           | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 13:15 |
| - | 0   | "anisotropic etching" near "liquid crystal substrate" | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 13:15 |
| - | 708 | "anisotropic etching" near "substrate"                | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 13:23 |
| - | 144 | (349/154).CCLS.                                       | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 13:26 |
| - | 10  | "injection hole" adj "substrate"                      | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 13:43 |
| - | 0   | "sealant" adj "glue, epoxy, solder"                   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 13:46 |
| - | 0   | "sealant material" adj "glue, epoxy, and solder"      | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 13:46 |
| - | 311 | "sealant" adj "epoxy"                                 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 13:54 |
| - | 3   | "liquid crystal" adj "microdisplays"                  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 14:22 |
| - | 83  | "testing" adj "liquid crystal display"                | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 14:29 |
| - | 0   | "testing" adj "liquid crystal micro display"          | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 14:27 |
| - | 0   | "testing" adj "sealing hole"                          | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 14:29 |

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| - | 0   | "testing" adj " liquid crystal sealing hole" | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 14:30 |
| - | 2   | "6330099"                                    | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 15:09 |
| - | 0   | (349/190 and testing).CCLS.                  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 15:18 |
| - | 0   | 349/190 adj testing                          | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 15:18 |
| - | 0   | 349/190 near testing                         | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 15:18 |
| - | 0   | "349/190" near "testing"                     | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 15:18 |
| - | 0   | "349/190" adj "testing"                      | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 15:18 |
| - | 475 | (438/15).CCLS.                               | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 15:21 |
| - | 98  | (injection hole) adj (glue)                  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/10/02 16:19 |

438/15 → Key to successful search  
because Applicant's methods  
are drawn from  
semiconductor technology  
< testing; failure analysis >

Joe